

Appl. No. : 09/397,952
Filed : September 17, 1999

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amended

forming an insulator element region on said substrate; and
transforming a portion of said conductive layer adjacent said insulator element region into a sidewall spacer after forming the insulator element region.

sub
E4

15. (Amended) A process of forming a gate structure on a semiconductor wafer comprising the steps of:

providing a semiconductor wafer having a channel region formed therein so as to define a source and a drain region and a gate structure comprised of an isolation layer positioned over said channel region and a conductive layer positioned over said isolation layer;

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forming a nitrogen-rich region by implanting nitrogen into said source and drain regions;

transforming a portion of said conductive layer adjacent said nitrogen-rich [insulator element] region into an oxide spacer;

combining a portion of said substrate with said nitrogen to form a nitride protective layer over said substrate; and

depositing a sidewall spacer over the oxide spacer.

REMARKS

Applicant has amended Claims 1 and 15 to clarify and to better protect the subject matter that Applicant regards as the invention. Applicant respectfully submits that the amendments add no new matter and are fully supported by the application as originally filed.

Rejections under 35 U.S.C. § 102(b)